

# Next-Generation NAND Flash Part Numbering System

Micron's part numbering system is available at [www.micron.com/numbering](http://www.micron.com/numbering)

## Next-Generation NAND Flash\*

MT

29F

2G

08

A

A

A

A

A

WP

-

xx

xx

x

ES

:

A

Micron Technology

Single-Supply Flash

29F = NAND Flash

29E = Enterprise NAND Flash

Density

1G = 1Gb

2G = 2Gb

4G = 4Gb

8G = 8Gb

16G = 16Gb

32G = 32Gb

64G = 64Gb

128G = 128Gb

256G = 256Gb

Device Width

01 = 1 bit

08 = 8 bits

16 = 16 bits

Level

Mark	Level
A	SLC
B	Reserved
C	MLC-2

Classification

Mark	Die	nCE	RnB	IO Channels
A	1	0	0	1
B	1	1	1	1
C	2	0	0	1
D	2	1	1	1
E	2	2	2	2
F	2	2	2	1
G				
H	4	1	1	1
J	4	2	2	1
K	4	2	2	2
L	4	4	4	1
M	4	4	4	2
N	4 + 4	2 + 2	2 + 2	1
P	8	1	1	1
Q	8	2	2	1
R	8	2	2	2
T	8	4	4	1
U	8	4	4	2
V				
W				
Y				

Design Revision (shrink)

Production Status

Blank = Production

ES = Engineering Samples

QS = Qualification Samples

MS = Mechanical Sample

Reserved for Future use.

Operating Temperature Range

Blank = Commercial (0°C to +70°C)

IT = Extended (-40°C to +85°C) (AKA ET)

WT = Wireless Temp (-25°C to +85°C)

Speed Grade (Synchronous)

Blank if no speed grade defined

20 = 100MT/s

15 = 133MT/s

12 = 166MT/s

Package Code

WP = 48-pin TSOP I (CPL version) (Pb-free)

WC = 48-pin TSOP I (OCPL version) (Pb-free)

HC = 63-ball VFBGA, 10.5 x 13 x 1.0

C3 = 52-pad ULGA, 12 x 17 x 0.65

C4 = 52-pad VLGA, 12 x 17 x 1.0 (SDP/DDP/QDP)

C5 = 52-pad VLGA, 14 x 18 x 1.0 (SDP/DDP/QDP)

C6 = 52-pad LLGA, 14 x 18 x 1.47 (DDP/QDP/BDP)

C7 = 48-pad LLGA, 12 x 20 x 1.47 (8DP)

C8 = 52-pad WLGA, 14 x 18 x 0.75 (DDP/QDP)

H1 = 100-ball VBGA (Pb-free), 12 x 18 x 1.0

H2 = 100-ball TBGA (Pb-free), 12 x 18 x 1.2

H3 = 100-ball LBGA, (Pb-free) 12 x 18 x 1.4 (DDP/QDP/BDP)

H4 = 63-ball VFBGA, 9 x 11 x 1

Interface

Mark	Interface
A	Async only
B	Sync/Async
D	SPi

Generation Feature Set

A = 1st set of device features

B = 2nd set of device features (rev only if different than 1st set)

C = 3rd set of device features (rev only if different)

D = 4th set of device features (rev only if different)

etc.

Operating Voltage Range

A = 3.3V (2.70-3.60V)

B = 1.8V (1.70-1.95V)

C = 3.3V (2.70-3.60V), VccQ 1.8V (1.70-1.95V)

D = 1.8V (1.65-3.6V) SIM

\*Contact Micron for help differentiating between standard and next-generation NAND offerings.

